WE CLAIM:

1. A method of fabricating a Bragg reflector comprising:

forming at least one structure layer and at least one sacrificial layer in alternating relation on a substrate;

etching the structure and sacrificial layers into at least one mesa protruding from the substrate;

forming a support layer on the at least one mesa leaving a portion of the structure and the sacrificial layers exposed; and

etching at least a portion of at least one of the exposed sacrificial layers to form a gap.

2. The method of claim 1 wherein forming a support layer on the at least one mesa comprises masking a portion of the mesa to prevent deposition of the support layer on the portion of the mesa.

3. The method of claim 2 wherein forming a support layer is depositing the support layer in a chemical vapor deposition process and wherein the mask is a dielectric mask.

4. The method of claim 1 wherein the material of the structure layer and the material of the support layer comprise substantially the same material.

5. The method of claim 1 wherein the structure layer material is different than a sacrificial layer material, and wherein etching at least a portion of at least one of the exposed sacrificial layers comprises etching the sacrificial layers without substantially etching the structure layers.

6. The method of claim 5 wherein etching further comprises etching without substantially etching the support layer.

7. The method of claim 1 wherein the at least one mesa has a sidewall, and wherein forming a support layer on the at least one mesa comprises forming the support layer on at least a portion of the sidewall.

8. The method of claim 1 wherein the sacrificial layer comprises a material selected from the group consisting of InGaAs, AlAs, and SiO_2 and the structure layer comprises a material selected from the group consisting of InP, GaAs, and Si.

9. The method of claim 8 wherein the support layer comprises a material selected from the group consisting of InP, GaAs, and Si.

10. The method of claim 1 further comprising doping at least a portion of the support layer to create an electrically conductive path.

11. The method of claim 1 further comprising doping at least a portion of the support layer to make at least the portion of the support layer electrically non-conductive.

12. A Bragg reflector comprising:

one or more first layers adjacent one or more second layers, the first and second layers having at least one sidewall, wherein the first and second layers define one or more gaps; and

a support layer formed over at a least portion of the sidewalls to support the second layers against intrusion into the one or more gaps.

13. The Bragg reflector of claim 12 wherein the second layers and the support layer comprise substantially the same material.

14. The Bragg reflector of claim 12 wherein at least a portion of the support layer is electrically conductive.

15. The Bragg reflector of claim 12 wherein at least a portion of the support layer is electrically non-conductive.

16. A distributed Bragg reflector comprising:

a substrate;

a plurality structure layers on the substrate each spaced apart by a gap, the structure layers each having edges; and

a support layer about a portion of the edges for supporting the structure layers.

17. The distributed Bragg reflector of claim 16 further comprising sacrificial layers between the structure layers, the sacrificial layers undercut to define the gaps.

18. The distributed Bragg reflector of claim 16 wherein the support layer comprises a material selected from the group consisting of InP, GaAs, and Si.

19. The distributed Bragg reflector of claim 16 wherein the structure layers comprise a material selected from the group consisting of InP, GaAs, Si.

20. The distributed Bragg reflector of claim 16 wherein the support layer covers at least a portion of a top of the structure layers.